## MC14175B

# **Quad Type D Flip-Flop**

The MC14175B quad type D flip—flop is constructed with MOS P—channel and N—channel enhancement mode devices in a single monolithic structure. Each of the four flip—flops is positive—edge triggered by a common clock input (C). An active—low reset input (R) asynchronously resets all flip—flops. Each flip—flop has independent Data (D) inputs and complementary outputs (Q and Q). These devices may be used as shift register elements or as type T flip—flops for counter and toggle applications.

#### **Features**

- Complementary Outputs
- Static Operation
- All Inputs and Outputs Buffered
- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Output Compatible with Two Low-Power TTL Loads or One Low-Power Schottky TTL Load
- Functional Equivalent to TTL 74175
- These Devices are Pb-Free and are RoHS Compliant
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable\*

#### MAXIMUM RATINGS (Voltages Referenced to V<sub>SS</sub>)

Parameter	Symbol	Value	Unit
DC Supply Voltage Range	$V_{DD}$	-0.5 to +18.0	V
Input or Output Voltage Range (DC or Transient)	V <sub>in</sub> , V <sub>out</sub>	-0.5 to V <sub>DD</sub> + 0.5	V
Input or Output Current (DC or Transient) per Pin	I <sub>in</sub> , I <sub>out</sub>	±10	mA
Power Dissipation per Package (Note 1)	P <sub>D</sub>	500	mW
Ambient Temperature Range	T <sub>A</sub>	-55 to +125	°C
Storage Temperature Range		-65 to +150	°C
Lead Temperature (8–Second Soldering)		260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Packages:  $-7.0 \text{ mW/}^{\circ}\text{C}$  From 65°C To 125°C This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.



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SOIC-16 D SUFFIX CASE 751B SOEIAJ-16 F SUFFIX CASE 966

#### **PIN ASSIGNMENT**

R [	1●	16	
Q0 [	2	15	] Q3
Q0 [	3	14	] <del>Q</del> 3
D0 [	4	13	] D3
D1 [	5	12	D2
Q1 [	6	11	] Q2
Q1 [	7	10	] Q2
v <sub>ss</sub> [	8	9	С

#### **MARKING DIAGRAMS**



SOIC-16

SOEIAJ-16

A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G = Pb-Free Package

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC14175BDG	SOIC-16 (Pb-Free)	48 Units/Rail
MC14175BDR2G	SOIC-16 (Pb-Free)	2500/Tape & Reel
NLV14175BDR2G*	SOIC-16 (Pb-Free)	2500/Tape & Reel
MC14175BFELG	SOEIAJ-16 (Pb-Free)	2000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **TRUTH TABLE**

	Inputs		Out		
Clock	Data	Reset	Q	Q	
	0	1	0	1	
	1	1	1	0	\
~	Х	1	Q	Q	No Change
Χ	X	0	0	1	Change



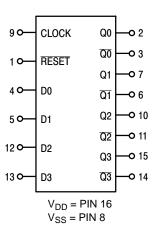


Figure 1. Block Diagram

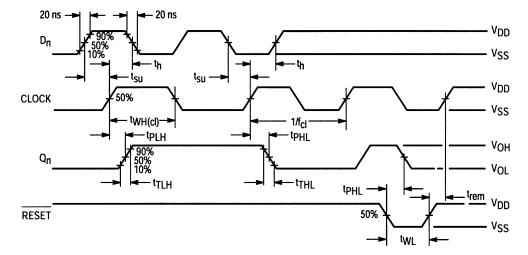


Figure 2. Timing Diagram

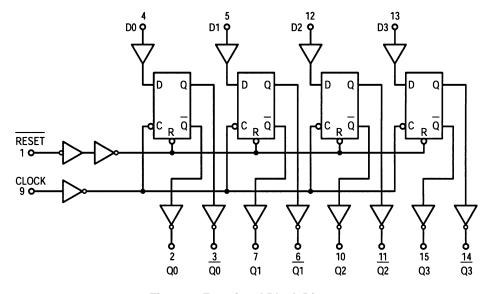


Figure 3. Functional Block Diagram

#### MC14175B

#### **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

				-55	-55°C 25°C			125	5°C		
Characteristic		Symbol	V <sub>DD</sub> Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	V <sub>OL</sub>	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
V <sub>in</sub> = 0 or V <sub>DD</sub>	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage (V <sub>O</sub> = 4.5 or 0.5 Vdc) (V <sub>O</sub> = 9.0 or 1.0 Vdc) (V <sub>O</sub> = 13.5 or 1.5 Vdc)	"0" Level	V <sub>IL</sub>	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V <sub>IH</sub>	5.0 10 15	3.5 7.0 11	1 1 1	3.5 7.0 11	2.75 5.50 8.25	111	3.5 7.0 11	1 1 1	Vdc
Output Drive Current $(V_{OH} = 2.5 \text{ Vdc})$ $(V_{OH} = 4.6 \text{ Vdc})$ $(V_{OH} = 9.5 \text{ Vdc})$ $(V_{OH} = 13.5 \text{ Vdc})$	Source	ІОН	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2		-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	1 1 1	-1.7 -0.36 -0.9 -2.4		mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	l <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2		0.51 1.3 3.4	0.88 2.25 8.8	1 1 1	0.36 0.9 2.4	1 1 1	mAdc
Input Current		l <sub>in</sub>	15	_	±0.1	-	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	ı	-	ı	_	5.0	7.5	-	ı	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	- - -	5.0 10 20	- - -	0.005 0.010 0.015	5.0 10 20	- - -	150 300 600	μAdc
Total Supply Current (Note (Dynamic plus Quiesce Per Package) (C <sub>L</sub> = 50 pF on all outp buffers switching)	ent,	I <sub>T</sub>	5.0 10 15	$I_{T} = (1.7 \ \mu \text{A/kHz}) \ \text{f} + I_{DD}$ $I_{T} = (3.4 \ \mu \text{A/kHz}) \ \text{f} + I_{DD}$ $I_{T} = (5.0 \ \mu \text{A/kHz}) \ \text{f} + I_{DD}$				μAdc			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
 Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
 The formulas given are for the typical characteristics only at 25°C.
 To calculate total supply current at loads other than 50 pF: I<sub>T</sub>(C<sub>L</sub>) = I<sub>T</sub>(50 pF) + (C<sub>L</sub> – 50) Vfk where: I<sub>T</sub> is in μA (per package), C<sub>L</sub> in pF, V = (V<sub>DD</sub> – V<sub>SS</sub>) in volts, f in kHz is input frequency, and k = 0.004.

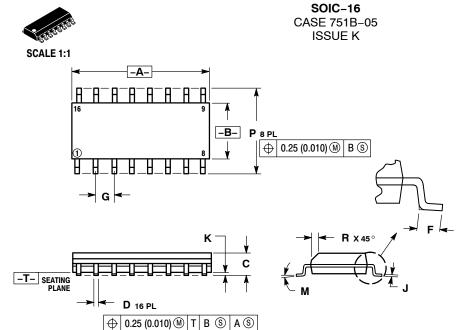
### MC14175B

### **SWITCHING CHARACTERISTICS** (Note 5) ( $C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$ )

Characteristic	Symbol	V <sub>DD</sub> Vdc	Min	Min (Note 6)		Unit
Output Rise and Fall Time $t_{TLH}$ , $t_{THL}$ = (1.35 ns/pF) $C_L$ + 32 ns $t_{TLH}$ , $t_{THL}$ = (0.6 ns/pF) $C_L$ + 20 ns $t_{TLH}$ , $t_{THL}$ = (0.4 ns/pF) $C_L$ + 20 ns	t <sub>TLH</sub> , t <sub>THL</sub>	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time — Clock to Q, Q $t_{PLH}$ , $t_{PHL}$ = (0.9 ns/pF) $C_L$ + 175 ns $t_{PLH}$ , $t_{PHL}$ = (0.36 ns/pF) $C_L$ + 72 ns $t_{PLH}$ , $t_{PHL}$ = (0.26 ns/pF) $C_L$ + 57 ns	t <sub>PLH</sub> , t <sub>PHL</sub>	5.0 10 15		220 90 70	400 160 120	ns
Propagation Delay Time — Reset to Q, Q $t_{PHL}$ = (0.9 ns/pF) $C_L$ + 280 ns $t_{PHL}$ = (0.36 ns/pF) $C_L$ + 112 ns $t_{PHL}$ = (0.26 ns/pF) $C_L$ + 87 ns	t <sub>PHL</sub> , t <sub>PLH</sub>	5.0 10 15		325 130 100	500 200 150	ns
Clock Pulse Width	twH	5.0 10 15	250 100 75	110 45 35	- - -	ns
Reset Pulse Width	t <sub>W</sub> ∟	5.0 10 15	200 80 60	100 40 30	- - -	ns
Clock Pulse Frequency	f <sub>cl</sub>	5.0 10 15	- - -	4.5 11 14	2.0 5.0 6.5	mHz
Clock Pulse Rise and Fall Time	t <sub>TLH</sub> , t <sub>THL</sub>	5.0 10 15	- - -	- - -	15 5.0 4.0	μs
Data Setup Time	t <sub>su</sub>	5.0 10 15	120 50 40	60 25 20	- - -	ns
Data Hold Time	t <sub>h</sub>	5.0 10 15	80 40 30	40 20 15	- - -	ns
Reset Removal Time	t <sub>rem</sub>	5.0 10 15	250 100 80	125 50 40	- - -	ns

<sup>5.</sup> The formulas given are for the typical characteristics only at 25°C.
6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

# **MECHANICAL CASE OUTLINE**



**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN MAX		MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40 1.25 (		0.016	0.049
G	1.27	BSC	0.050	BSC
7	0.19	0.25	0.008	0.009
K	0.10	0.10 0.25		0.009
M	0°	7°	0°	7°
Р	5.80 6.20		0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.		PIN 1.		PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.			ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR			8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE		CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.		11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER		CATHODE	12.		12.			
13.	BASE		CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	SOI DEDING	FOOTPRINT
14.			NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	FOOTFRINT
15.	EMITTER		ANODE	15.	EMITTER, #4	15.	BASE, #1	8	ЗX
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	<b>-</b> 6	.40 ────
								-	-
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 <
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				,
2.	DRAIN. #1		CATHODE	2.	COMMON DRAIN (OUTPUT	)		. 🗀 1	16
3.	DRAIN, #2		CATHODE	3.	COMMON DRAIN (OUTPUT			<b>,</b>	'' 🖳
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,			
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	)	16	5X <b>T</b>	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT		0.5		' <u> </u>
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPUT		0.0		
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT				
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	,			¦
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT	)			↓ PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT				<u>+-+</u>
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH	,			
	•							□ <sub>8</sub>	9 + - + -
								•	,
									BINENIOLONIO MILLINETTE
									DIMENSIONS: MILLIMETERS

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